

## **IN THE CLAIMS**

Claims 1-23 (Canceled).

24 (Currently Amended).     A device comprising:  
a semiconductor substrate having at least one layer with conductive metal lines thereon; and  
a porous carbon doped oxide between the metal lines, said porous carbon doped oxide having a facing dielectric surface abutting a conductive metal line, the conductive metal line having a smoother sidewall than the facing dielectric surface.

25 (Previously Presented).     The device of claim 24 wherein the carbon doped oxide is at least 50% porous.

26 (Currently Amended).     The device of claim 24 wherein said ~~conductive doped~~ oxide is over a conductive layer.

27 (Previously Presented).     The device of claim 25 wherein said carbon doped oxide has a dielectric constant below about 3.0.